Octal 3-State Noninverting D Flip-Flop

High-Performance Silicon-Gate CMOS

MC74HC574A

The MC74HC574A is identical in pinout to the LS574. The device inputs are compatible with standard CMOS outputs; with pull–up resistors, they are compatible with LSTTL outputs.

Data meeting the set-up time is clocked to the outputs with the rising edge of the Clock. The Output Enable input does not affect the states of the flip-flops but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

The HC574A is identical in function to the HC374A but has the flip–flop inputs on the opposite side of the package from the outputs to facilitate PC board layout.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 µA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 266 FETs or 66.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

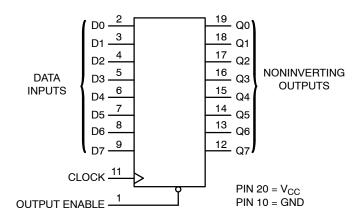


Figure 1. Logic Diagram

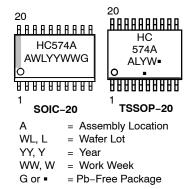


CASE 751D

TSSOP-20 DT SUFFIX CASE 948E

OUTPUT			_
ENABLE 🗖	10	20	
D0 🗖	2	19	🗖 Q0
D1 🗖	3	18	🗖 Q1
D2 🗖	4	17	🗖 Q2
D3 🗖	5	16	🗖 Q3
D4 🗖	6	15	🗖 Q4
D5 🗖	7	14	🗖 Q5
D6 🗖	8	13	🗖 Q6
D7 🗖	9	12	🗖 Q7
GND 🗖	10	11	🗀 сгоск

MARKING DIAGRAMS



(Note: Microdot may be in either location)

FUNCTION TABLE Inputs Output OE Clock D Q L н Н L 1 L L L,H, ∕_ Х L No Change н Х Х 7

X = Don't Care

Z = High Impedance

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

Design Criteria	Value	Units
Internal Gate Count*	66.5	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рJ

*Equivalent to a two-input NAND gate.

MAXIMUM RATINGS

Symbol	F	Parameter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		–0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	(Note 1)	–0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current		±20	mA
Ι _{ΟΚ}	DC Output Diode Current		±35	mA
Ι _Ο	DC Output Sink Current		±35	mA
I _{CC}	DC Supply Current per Supply Pin		±75	mA
I _{GND}	DC Ground Current per Ground Pin		±75	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case f	or 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	SOIC TSSOP	96 128	°C/W
PD	Power Dissipation in Still Air at 85°C	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 4000 > 300 > 1000	V
I _{Latchup}	Latchup Performance	Above V_{CC} and Below GND at 85 °C (Note 5)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

I_O absolute maximum rating must be observed.
 Tested to EIA/JESD22-A114-A.

3. Tested to EIA/JESD22-A115-A.

4. Tested to JESD22-C101-A.

5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	(Referenced to GND)	2.0	6.0	V
V _I , V _O	DC Input Voltage, Output Voltage	(Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types		-55	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 2)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

6. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

			V _{CC}	Guara	anteed Lim	it	
Symbol	Parameter	Test Conditions	V	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$\begin{split} V_{out} &= V_{CC} - 0.1 \text{ V} \\ I_{out} &\leq 20 \ \mu \text{A} \end{split}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 V$ $ I_{out} \le 20 \mu A$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \ \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
V _{OH}	Minimum High-Level Output Voltage	$\label{eq:Vin} \begin{array}{ll} V_{in} = V_{IH} & \qquad & \left I_{out}\right \leq 2.4 \text{ mA} \\ \left I_{out}\right \leq 6.0 \text{ mA} \\ \left I_{out}\right \leq 7.8 \text{ mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	V
V _{OL}	Maximum Low-Level Output Voltage	$ \begin{aligned} V_{in} &= V_{IL} \\ I_{out} &\leq 20 \ \mu A \end{aligned} $	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\label{eq:Vin} \begin{array}{ll} V_{in} = V_{IL} & \left \begin{array}{c} I_{out} \right \leq 2.4 \text{ mA} \\ \left \begin{array}{c} I_{out} \right \leq 6.0 \text{ mA} \\ \left \begin{array}{c} I_{out} \right \leq 7.8 \text{ mA} \end{array} \end{array} \right $	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μΑ
I _{OZ}	Maximum Three-State Leakage Current	$\begin{array}{l} Output \text{ in High-Impedance State} \\ V_{in} = V_{IL} \text{ or } V_{IH} \\ V_{out} = V_{CC} \text{ or GND} \end{array}$	6.0	±0.5	±5.0	±10	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $I_{out} = 0 \ \mu A$	6.0	4.0	40	160	μA

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Parameter	V _{CC}	Guara			
	v	–55 to 25°C	≤ 85°C	≤ 125°C	Unit
Maximum Clock Frequency (50% Duty Cycle) (Figures 2 and 5)	2.0 3.0 4.5 6.0	6.0 15 30 35	4.8 10 24 28	4.0 8.0 20 24	MHz
Maximum Propagation Delay, Clock to Q (Figures 2 and 5)	2.0 3.0 4.5 6.0	160 105 32 27	200 145 40 34	240 190 48 41	ns
Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	2.0 3.0 4.5 6.0	150 100 30 26	190 125 38 33	225 150 45 38	ns
Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	2.0 3.0 4.5 6 0	140 90 28 24	175 120 35 30	210 140 42 36	ns
Maximum Output Transition Time, any Output (Figures 2 and 5)	2.0 3.0 4.5 6.0	60 27 12 10	75 32 15 13	90 36 18 15	ns
Maximum Input Capacitance	•	10	10	10	pF
Maximum Three-State Output Capacitance, Output in High- State	-Impedance	15	15	15	pF
	Maximum Clock Frequency (50% Duty Cycle) (Figures 2 and 5) Maximum Propagation Delay, Clock to Q (Figures 2 and 5) Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6) Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6) Maximum Output Transition Time, any Output (Figures 2 and 5) Maximum Input Capacitance Maximum Three–State Output Capacitance, Output in High-	ParameterVMaximum Clock Frequency (50% Duty Cycle) (Figures 2 and 5)2.0 3.0 4.5 6.0Maximum Propagation Delay, Clock to Q (Figures 2 and 5)2.0 3.0 4.5 6.0Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)2.0 3.0 4.5 6.0Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)2.0 3.0 4.5 6.0Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)2.0 3.0 4.5 6.0Maximum Output Transition Time, any Output (Figures 2 and 5)2.0 3.0 4.5 6.0Maximum Input Capacitance3.0 4.5 6.0Maximum Input CapacitanceMaximum Three-State Output Capacitance, Output in High-Impedance	Parameter V -55 to 25°C Maximum Clock Frequency (50% Duty Cycle) (Figures 2 and 5) 2.0 6.0 Maximum Propagation Delay, Clock to Q (Figures 2 and 5) 2.0 160 Maximum Propagation Delay, Clock to Q (Figures 2 and 5) 2.0 160 Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6) 2.0 150 Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6) 2.0 150 Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6) 2.0 140 Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6) 2.0 140 Maximum Propagation Delay, Output Enable to Q (Figures 2 and 5) 2.0 140 Maximum Output Transition Time, any Output (Figures 2 and 5) 2.0 6.0 Maximum Input Capacitance 10 10 Maximum Input Capacitance 10 15	ParameterV-55 to 25° C $\leq 85^{\circ}$ CMaximum Clock Frequency (50% Duty Cycle) (Figures 2 and 5)2.0 3.06.0 154.8 10 4.5Maximum Propagation Delay, Clock to Q (Figures 2 and 5)2.0 3.0160 145 32 4.5200 3.0 105Maximum Propagation Delay, Clock to Q (Figures 2 and 5)2.0 4.5160 32 4.5145 4.5 32 40 6.0200 145 145Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)2.0 3.0 100 125 4.5150 30 38 6.0190 125 338 6.0Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)2.0 3.0 140 3.0 120 120150 3.0 3.0 120 120190 125 3.0 3.0 120 120Maximum Output Transition Time, any Output (Figures 2 and 5)2.0 3.0 3.0 100121 13Maximum Input Capacitance1010Maximum Input Capacitance1010	ParameterV-55 to 25° C $\leq 85^{\circ}$ C $\leq 125^{\circ}$ CMaximum Clock Frequency (50% Duty Cycle) (Figures 2 and 5)2.0 3.0 6.0 4.5 4.8 30 4.0 8.0 24 Maximum Propagation Delay, Clock to Q (Figures 2 and 5)2.0 3.0 160 145 200 240 Maximum Propagation Delay, Clock to Q (Figures 3 and 6)2.0 4.5 160 3.0 200 145 240 145 Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)2.0 3.0 150 145 190 125 225 150 Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)2.0

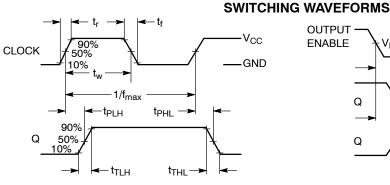
AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$; Input $t_r = t_f = 6.0 \text{ ns}$)

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Enabled Output)*	24	pF

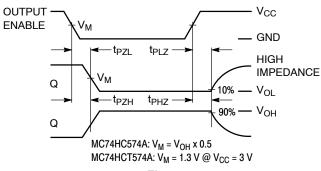
*Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}.

TIMING REQUIREMENTS (C_L = 50 pF; Input $t_r = t_f = 6.0$ ns)

				Guaranteed Limit						
			V _{cc}	–55 to	25°C	≤ 8	5°C	≤ 12	5°C	
Symbol	Parameter	Figure	Volts	Min	Max	Min	Max	Min	Max	Unit
t _{su}	Minimum Setup Time, Data to Clock	4	2.0 3.0 4.6 6.0	50 40 10 9.0		65 50 13 11		75 60 15 13		ns
t _h	Minimum Hold Time, Clock to Data	4	2.0 3.0 4.5 6.0	5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		5.0 5.0 5.0 5.0		ns
t _w	Minimum Pulse Width, Clock	2	2.0 3.0 4.5 6.0	75 60 15 13		95 80 19 16		110 90 22 19		ns
t _r , t _f	Maximum Input Rise and Fall Times	2	2.0 3.0 4.5 6.0		1000 800 500 400		1000 800 500 400		1000 800 500 400	ns





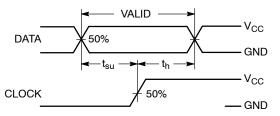




OUTPUT

TEST POINT

 C_L^*





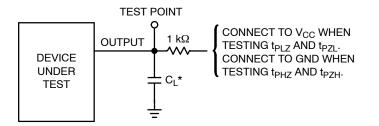


*Includes all probe and jig capacitance.

DEVICE

UNDER

TEST



*Includes all probe and jig capacitance.



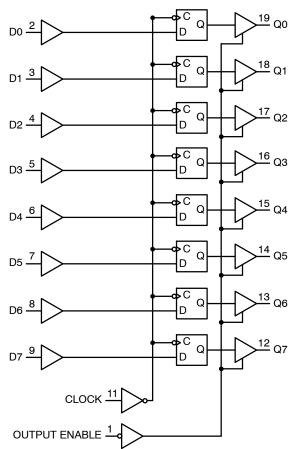
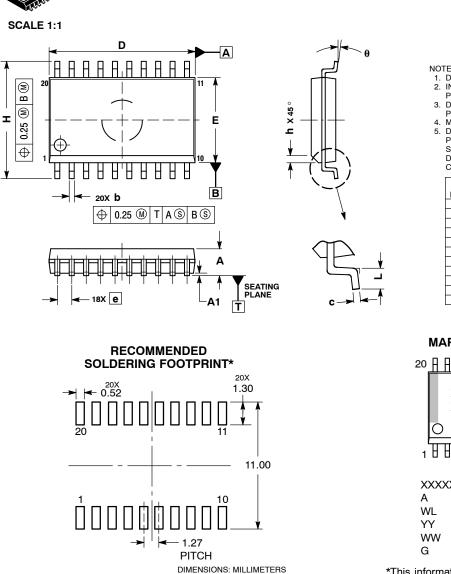


Figure 7. Expanded Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC574ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Tube
MC74HC574ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HC574ADTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel
NLV74HC574ADTR2G*	TSSOP-20 (Pb-Free)	2500 Tape & Reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DUSEM

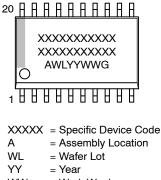
NOTES:

SOIC-20 WB CASE 751D-05 ISSUE H

- 1. DIMENSIONS ARE IN MILLIMETERS. 2. INTERPRET DIMENSIONS AND TOLERANCES
- PER ASME Y14.5M, 1994. 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS
DIM	MIN	MAX
Α	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
C	0.23	0.32
D	12.65	12.95
Е	7.40	7.60
е	1.27	BSC
Н	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0 °	7 °

GENERIC **MARKING DIAGRAM***



= Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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